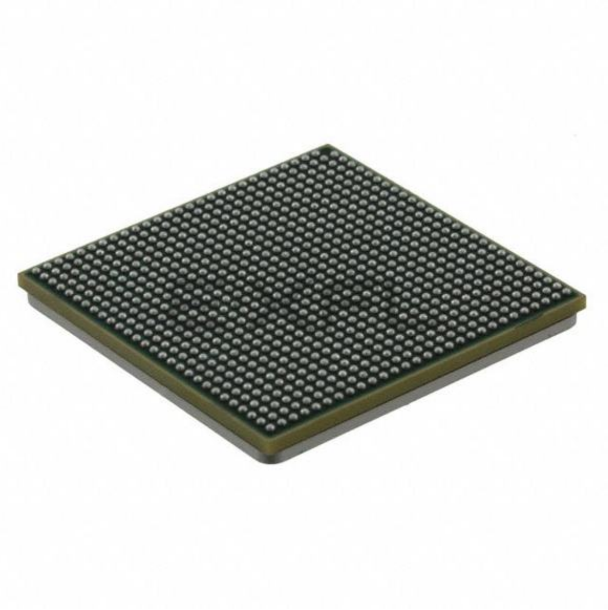
NXP USA Inc. - MPC8548VTATGB Datasheet



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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8548vtatgb

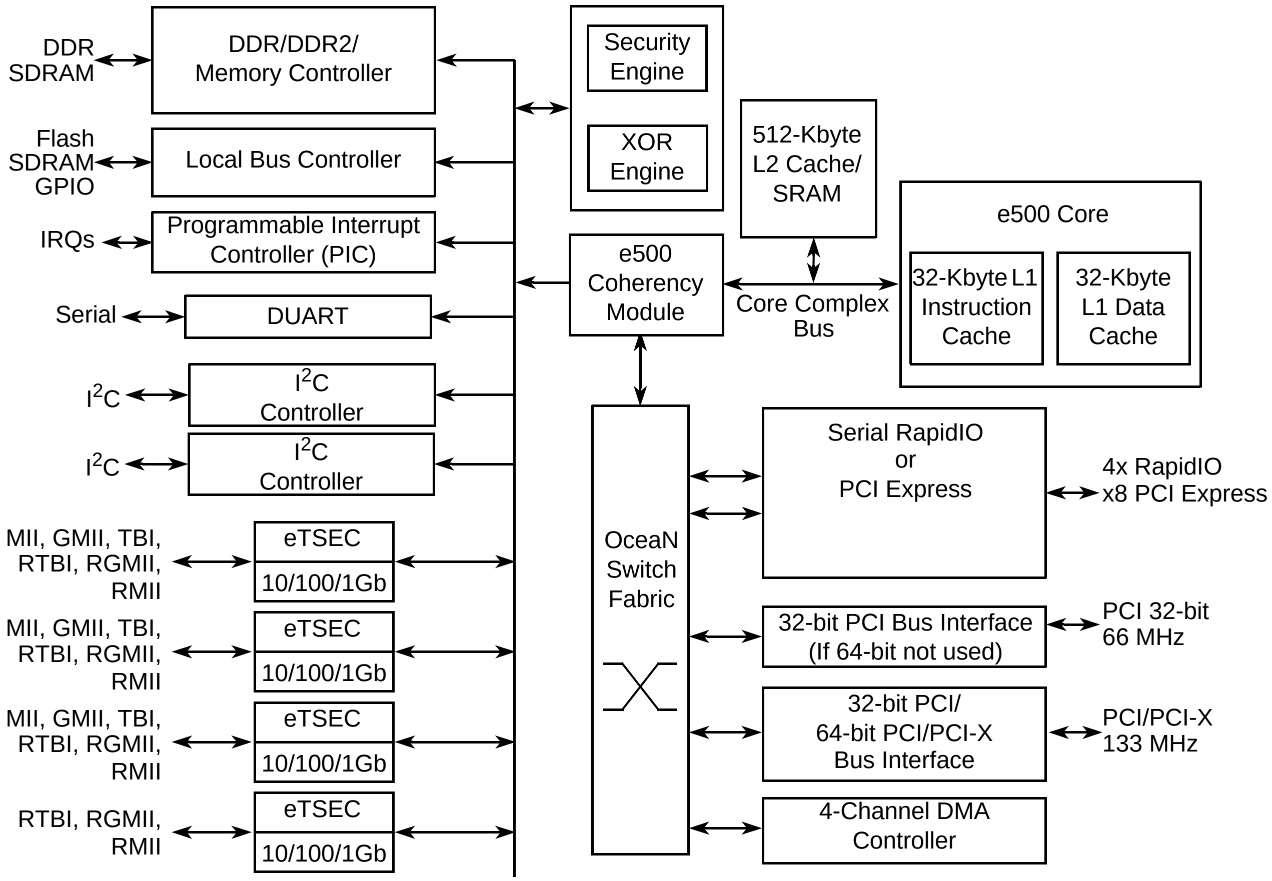


Figure 1. Device Block Diagram

1.1 Key Features

The following list provides an overview of the device feature set:

- High-performance 32-bit core built on Power Architecture® technology.
    - 32-Kbyte L1 instruction cache and 32-Kbyte L1 data cache with parity protection. Caches can be locked entirely or on a per-line basis, with separate locking for instructions and data.
    - Signal-processing engine (SPE) APU (auxiliary processing unit). Provides an extensive instruction set for vector (64-bit) integer and fractional operations. These instructions use both the upper and lower words of the 64-bit GPRs as they are defined by the SPE APU.
    - Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.
    - 36-bit real addressing
    - Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.
    - Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte to 4-Gbyte page sizes.
    - Enhanced hardware and software debug support

  - Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 512-Kbyte L2 cache/SRAM
  - Flexible configuration.
  - Full ECC support on 64-bit boundary in both cache and SRAM modes
  - Cache mode supports instruction caching, data caching, or both.
  - External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
  - 1, 2, or 4 ways can be configured for stashing only.
  - Eight-way set-associative cache organization (32-byte cache lines)
  - Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  - Global locking and Flash clearing done through writes to L2 configuration registers
  - Instruction and data locks can be Flash cleared separately.
  - SRAM features include the following:
    - I/O devices access SRAM regions by marking transactions as snoopable (global).
    - Regions can reside at any aligned location in the memory map.
    - Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
  - Eight local access windows define mapping within local 36-bit address space.
  - Inbound and outbound ATMUs map to larger external address spaces.
    - Three inbound windows plus a configuration window on PCI/PCI-X and PCI Express
    - Four inbound windows plus a default window on RapidIO™
    - Four outbound windows plus default translation for PCI/PCI-X and PCI Express
    - Eight outbound windows plus default translation for RapidIO with segmentation and sub-segmentation support
- DDR/DDR2 memory controller
  - Programmable timing supporting DDR and DDR2 SDRAM
  - 64-bit data interface
  - Four banks of memory supported, each up to 4 Gbytes, to a maximum of 16 Gbytes
  - DRAM chip configurations from 64 Mbits to 4 Gbits with ×8/×16 data ports
  - Full ECC support
  - Page mode support
    - Up to 16 simultaneous open pages for DDR

  - AESU—Advanced Encryption Standard unit
    - Implements the Rijndael symmetric key cipher
    - ECB, CBC, CTR, and CCM modes
    - 128-, 192-, and 256-bit key lengths
  - AFEU—ARC four execution unit
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - MDEU—message digest execution unit
    - SHA with 160- or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - KEU—Kasumi execution unit
    - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
    - Also supports A5/3 and GEA-3 algorithms
  - RNG—random number generator
  - XOR engine for parity checking in RAID storage applications
- Dual I^{2}C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^{2}C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^{2}C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^{2}C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Three protocol engines available on a per chip select basis:
    - General-purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)

Table 1. Absolute Maximum Ratings [1] (continued)

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The –0.3 to 2.75 V range is for DDR and –0.3 to 1.98 V range is for DDR2.
3. The 3.63 V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75 V maximum applies. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
4. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD}	1.1 V ± 55 mV	V	—
PLL supply voltage		AV_{DD}	1.1 V ± 55 mV	V	1
Core power supply for SerDes transceivers		SV_{DD}	1.1 V ± 55 mV	V	—
Pad power supply for SerDes transceivers		XV_{DD}	1.1 V ± 55 mV	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	4
		TV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	—	4
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	3
Local bus I/O voltage		BV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	—
Input voltage	DDR and DDR2 DRAM signals	MV_{IN}	GND to GV_{DD}	V	2
	DDR and DDR2 DRAM reference	MV_{REF}	GND to $GV_{DD}/2$	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	3

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} – 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.15$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} – 0.15$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, RMII, TBI, and RTBI are specified in "Section 8, "Enhanced Three-Speed Ethernet (eTSEC)."

9.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	3.13	3.47	V
Output high voltage (OV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.10	OV_{DD} + 0.3	V
Output low voltage (OV_{DD} =Min, I_{OL} = 1.0 mA)	V_{OL}	GND	0.50	V
Input high voltage	V_{IH}	2.0	—	V
Input low voltage	V_{IL}	—	0.90	V
Input high current (OV_{DD} = Max, $V_{IN}{}^{1}$ = 2.1 V)	I_{IH}	—	40	μA
Input low current (OV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 37. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	0.72	2.5	8.3	MHz	2, 3, 4
MDC period	t_{MDC}	120.5	—	1389	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$16 \times t_{CCB}$	—	—	ns	5
MDC to MDIO delay	t_{MDKHDX}	$(16 \times t_{CCB} \times 8) - 3$	—	$(16 \times t_{CCB} \times 8) + 3$	ns	5
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	4

Table 42. Local Bus Timing Parameters—PLL Bypassed (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKL2}$	–1.3	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKLOV1}$	—	–0.3	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKLOV2}$	—	–0.1	ns	4
Local bus clock to address valid for LAD	$t_{LBKLOV3}$	—	0	ns	4
Local bus clock to LALE assertion	$t_{LBKLOV4}$	—	0	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKLOX1}$	–3.7	—	ns	4
Output hold from local bus clock for LAD/LDP	$t_{LBKLOX2}$	–3.7	—	ns	4
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKLOZ1}$	—	0.2	ns	7
Local bus clock to output high impedance for LAD/LDP	$t_{LBKLOZ2}$	—	0.2	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to local bus clock for PLL bypass mode. Timings may be negative with respect to the local bus clock because the actual launch and capture of signals is done with the internal launch/capture clock, which precedes LCLK by t_{LBKHKT}.
3. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
4. All signals are measured from $BV_{DD}/2$ of the rising edge of local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
5. Input timings are measured at the pin.
6. The value of t_{LBOTOT} is the measurement of the minimum time between the negation of LALE and any change in LAD.
7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
8. Guaranteed by characterization.
9. Guaranteed by design.

Table 46. I^{2}C AC Electrical Specifications (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V	—
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I^{2}C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I^{2}C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I^{2}C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. As a transmitter, the device provides a delay time of at least 300 ns for the SDA signal (see the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL to avoid unintended generation of Start or Stop condition. When the device acts as the I^{2}C bus master while transmitting, the device drives both SCL and SDA. As long as the load on SCL and SDA are balanced, the device would not cause unintended generation of Start or Stop condition. Therefore, the 300 ns SDA output delay time is not a concern. If, under some rare condition, the 300 ns SDA output delay time is required for the device as a transmitter, the following setting is recommended for the FDR bit field of the I2CFDR register to ensure both the desired I^{2}C SCL clock frequency and SDA output delay time are achieved, assuming that the desired I^{2}C SCL clock frequency is 400 kHz and the Digital Filter Sampling Rate Register (I2CDFSRR) is programmed with its default setting of 0x10 (decimal 16):

I^{2}C source clock frequency	333 MHz	266 MHz	200 MHz	133 MHz
FDR bit setting	0x2A	0x05	0x26	0x00
Actual FDR divider selected	896	704	512	384
Actual I^{2}C SCL frequency generated	371 kHz	378 kHz	390 kHz	346 kHz

   For the detail of I^{2}C frequency calculation, see *Determining the I^{2}C Frequency Divider Ratio for SCL* (AN2919). Note that the I^{2}C source clock frequency is half of the CCB clock frequency for the device.
3. The maximum t_{I2DXKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. Guaranteed by design.

Figure 33 provides the AC test load for the I^{2}C.

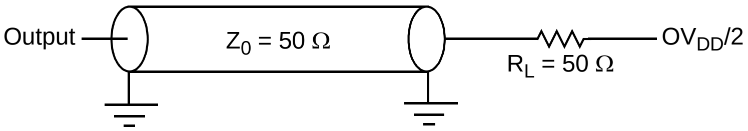


Figure 33. I^{2}C AC Test Load

This table provides the PCI AC timing specifications at 66 MHz.

Table 52. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
CLK to output valid	t_{PCKHOV}	—	6.0	ns	2, 3
Output hold from CLK	t_{PCKHOX}	2.0	—	ns	2, 10
CLK to output high impedance	t_{PCKHOZ}	—	14	ns	2, 4, 11
Input setup to CLK	t_{PCIVKH}	3.0	—	ns	2, 5, 10
Input hold from CLK	t_{PCIXKH}	0	—	ns	2, 5, 10
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ [9] setup time	t_{PCRVRH}	$10 \times t_{SYS}$	—	clocks	6, 7, 11
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	7, 11
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	8, 11

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI/PCI-X timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the SYSCLK clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI/PCI-X timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. All PCI signals are measured from $OV_{DD}/2$ of the rising edge of SYSCLK or PCI_CLK*n* to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V PCI signaling levels.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Input timings are measured at the pin.
6. The timing parameter t_{SYS} indicates the minimum and maximum CLK cycle times for the various specified frequencies. The system clock period must be kept within the minimum and maximum defined ranges. For values see Section 20, "Clocking."
7. The setup and hold time is with respect to the rising edge of $\overline{\text{HRESET}}$.
8. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI 2.2 Local Bus Specifications*.
9. The reset assertion timing requirement for $\overline{\text{HRESET}}$ is 100 μs.
10. Guaranteed by characterization.
11. Guaranteed by design.

Figure 35 provides the AC test load for PCI and PCI-X.

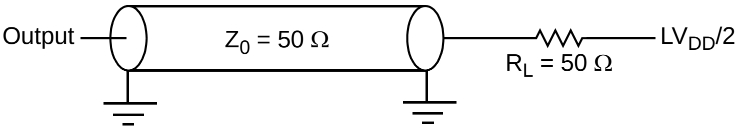


Figure 35. PCI/PCI-X AC Test Load

Table 54. PCI-X AC Timing Specifications at 133 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
$\overline{\text{HRESET}}$ to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 12

Notes:

1. See the timing measurement conditions in the *PCI-X 1.0a Specification*.
2. Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.
3. Setup time for point-to-point signals applies to $\overline{\text{REQ}}$ and $\overline{\text{GNT}}$ only. All other signals are bused.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.
6. Maximum value is also limited by delay to the first transaction (time for $\overline{\text{HRESET}}$ high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of HRESET must be negated no later than two clocks before the first $\overline{\text{FRAME}}$ and must be floated no later than one clock before $\overline{\text{FRAME}}$ is asserted.
7. A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.
8. Device must meet this specification independent of how many outputs switch simultaneously.
9. The timing parameter t_{PCIVKH} is a minimum of 1.4 ns rather than the minimum of 1.2 ns in the *PCI-X 1.0a Specification.*
10. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*
11. Guaranteed by characterization.
12. Guaranteed by design.

of a balanced interchange circuit and ground. In this example, for SerDes output, $V_{cm\_out} = V_{SD\_TX} + V_{\overline{SD\_TX}} = (A + B)/2$, which is the arithmetic mean of the two complimentary output voltages within a differential pair. In a system, the common mode voltage may often differ from one component's output to the other's input. Sometimes, it may be even different between the receiver input and driver output circuits within the same component. It is also referred to as the DC offset.

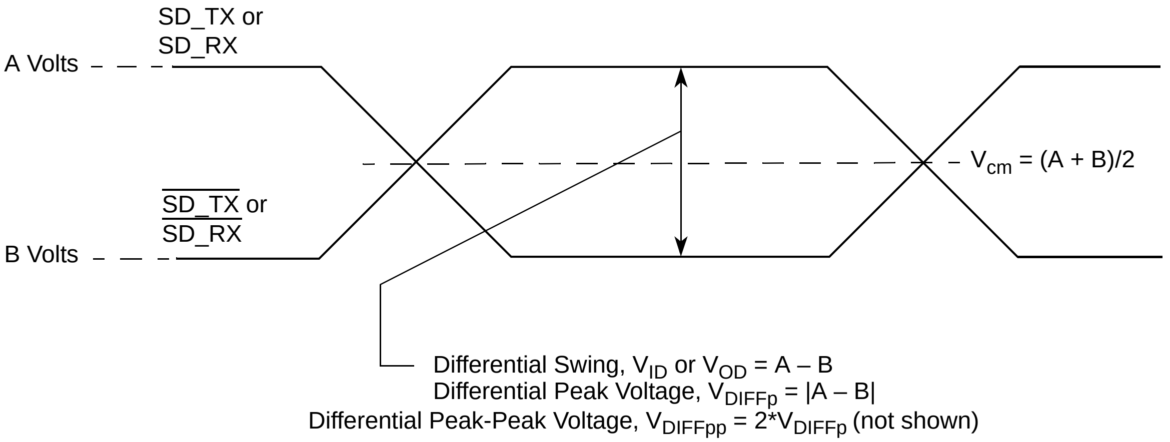


Figure 38. Differential Voltage Definitions for Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (current mode logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and $\overline{\text{TD}}$, has a swing that goes between 2.5 and 2.0 V. Using these values, the peak-to-peak voltage swing of each signal (TD or $\overline{\text{TD}}$) is 500 mVp-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 and –500 mV, in other words, V_{OD} is 500 mV in one phase and –500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage ($V_{DIFFp\text{-}p}$) is 1000 mVp-p.

16.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks inputs are SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ for PCI Express and serial RapidIO.

The following sections describe the SerDes reference clock requirements and some application information.

16.2.1 SerDes Reference Clock Receiver Characteristics

Figure 39 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for XV_{DD_SRDS2} are specified in Table 1 and Table 2.
- SerDes Reference clock receiver reference circuit structure:

to AC-coupling. Its value could be ranged from 140 to 240 Ω depending on the clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50-Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the SerDes reference clock's differential input amplitude requirement (between 200 and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω. Consult a clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.

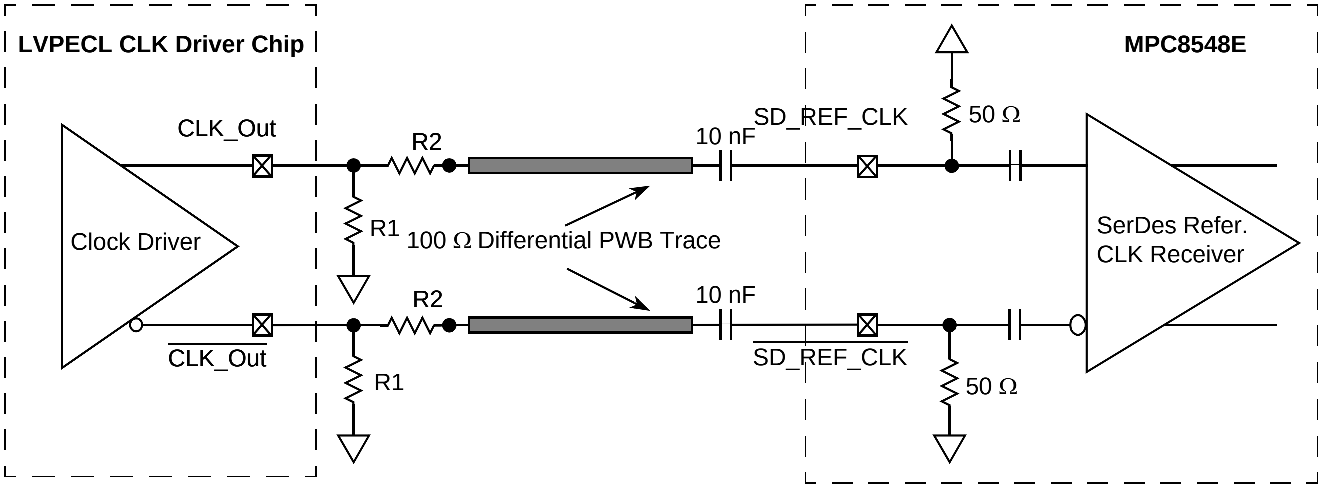


Figure 45. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

Figure 46 shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with the SerDes reference clock input's DC requirement.

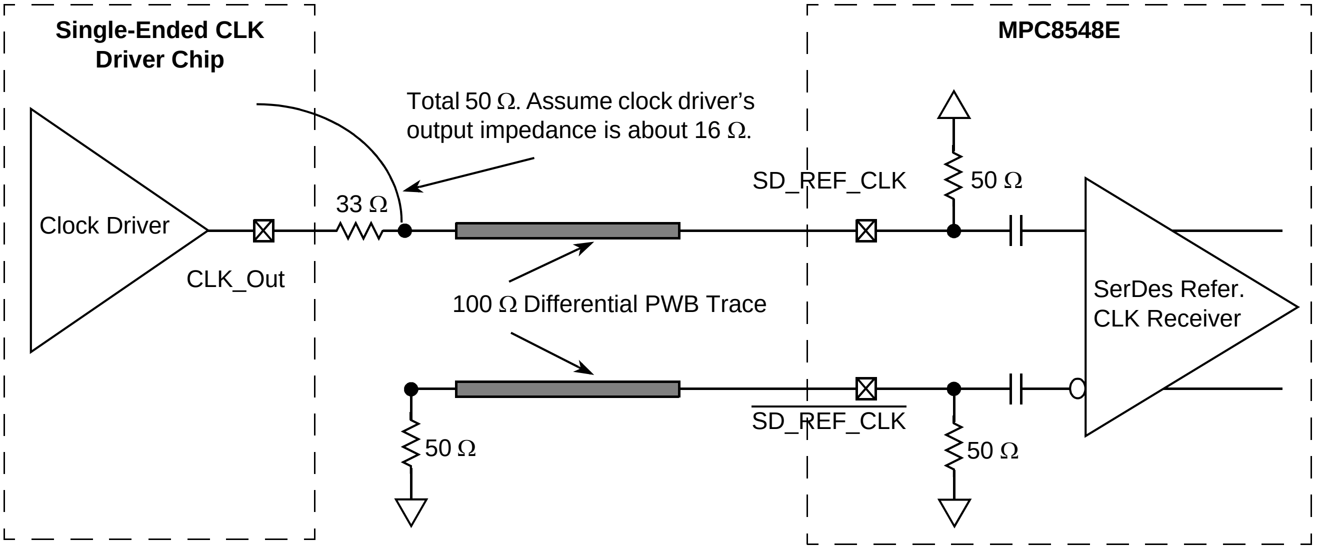


Figure 46. Single-Ended Connection (Reference Only)

18.8 Receiver Eye Diagrams

For each baud rate at which an LP-serial receiver is specified to operate, the receiver shall meet the corresponding bit error rate specification (Table 66, Table 67, and Table 68) when the eye pattern of the receiver test signal (exclusive of sinusoidal jitter) falls entirely within the unshaded portion of the receiver input compliance mask shown in Figure 54 with the parameters specified in Table 69. The eye pattern of the receiver test signal is measured at the input pins of the receiving device with the device replaced with a 100-Ω ± 5% differential resistive load.

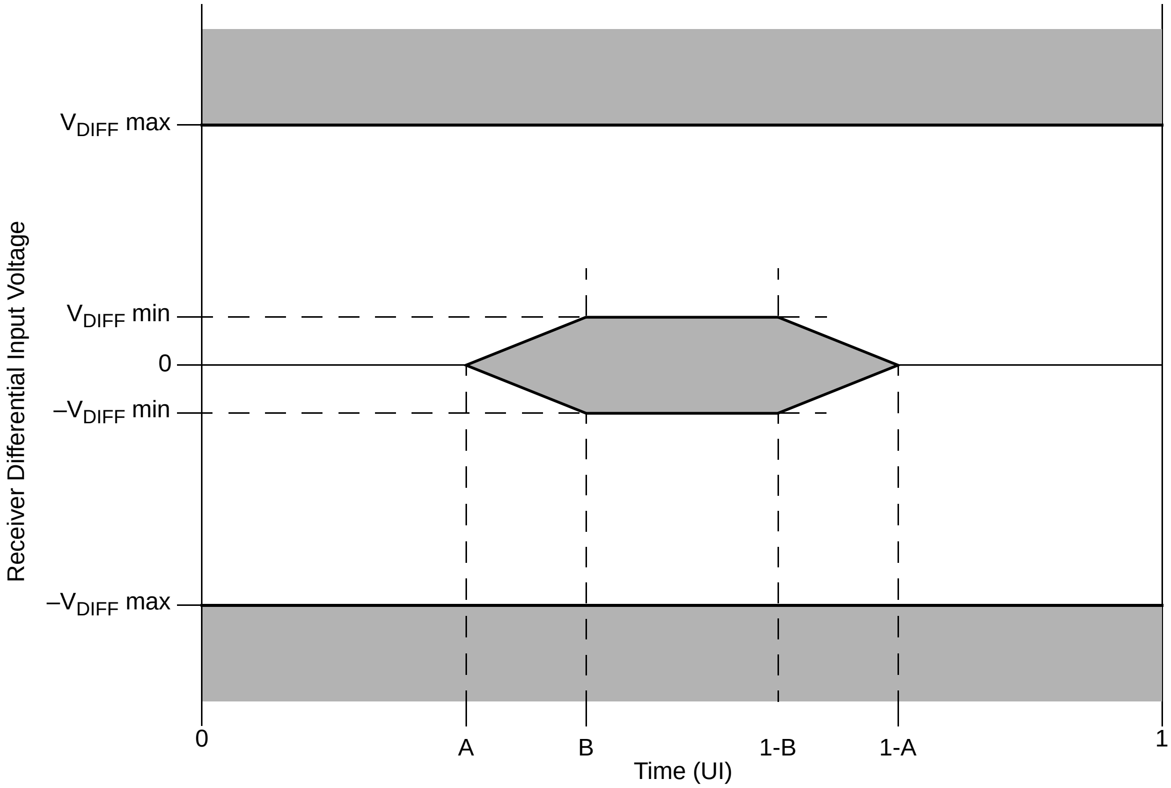


Figure 54. Receiver Input Compliance Mask

Table 69. Receiver Input Compliance Mask Parameters Exclusive of Sinusoidal Jitter

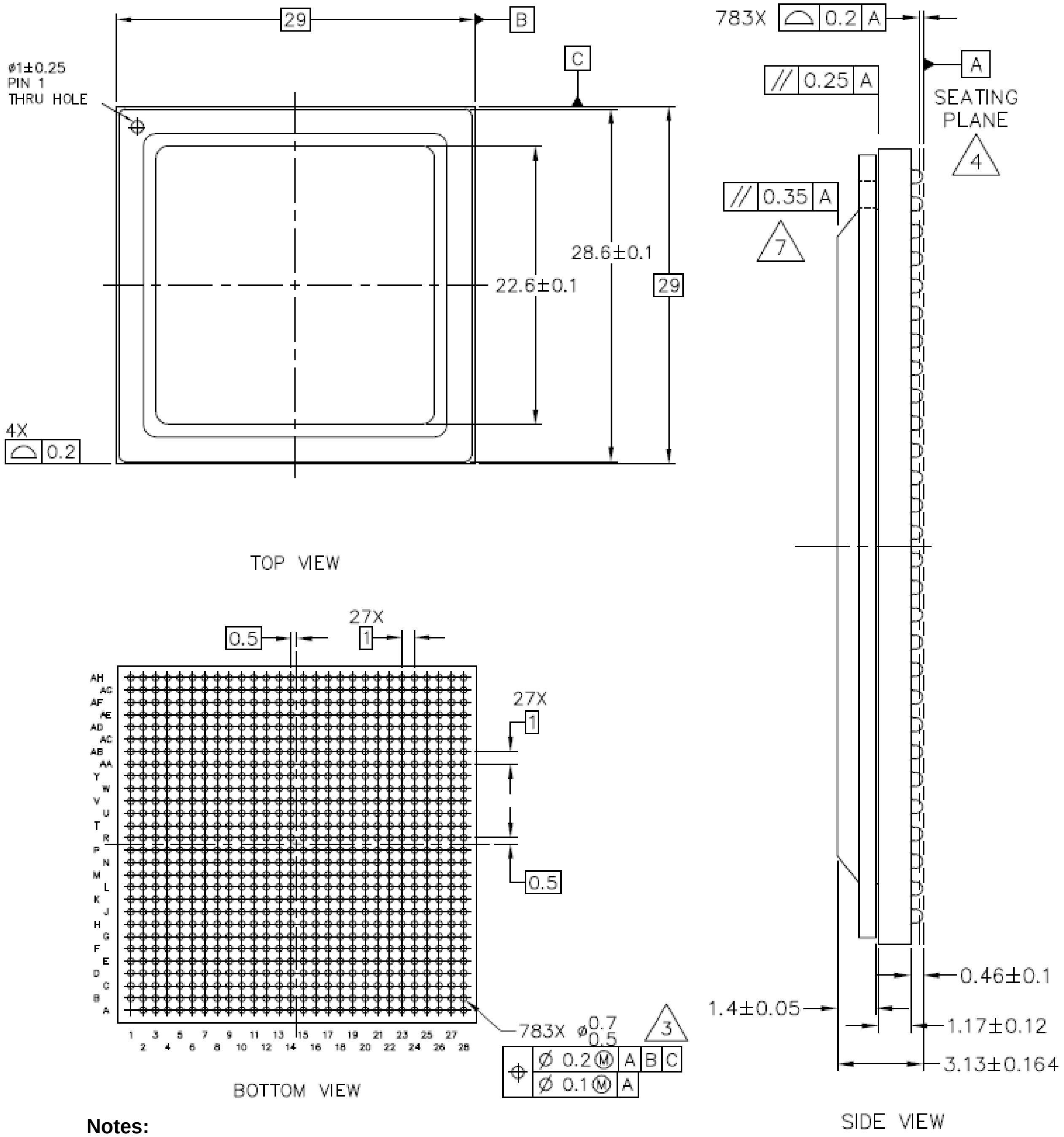
Receiver Type	V_{DIFF}min (mV)	V_{DIFF}max (mV)	A (UI)	B (UI)
1.25 GBaud	100	800	0.275	0.400
2.5 GBaud	100	800	0.275	0.400
3.125 GBaud	100	800	0.275	0.400

18.9 Measurement and Test Requirements

Since the LP-serial electrical specification are guided by the XAUI electrical interface specified in Clause 47 of IEEE Std. 802.3ae-2002, the measurement and test requirements defined here are similarly guided by Clause 47. Additionally, the CJPAT test pattern defined in Annex 48A of IEEE Std.

Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement shall exclude any effect of mark on top surface of package.
6. All dimensions are symmetric across the package center lines unless dimensioned otherwise.



Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Capacitors may not be present on all devices.
6. Caution must be taken not to short capacitors or exposed metal capacitor pads on package top.
7. Parallelism measurement shall exclude any effect of mark on top surface of package.
8. All dimensions are symmetric across the package center lines unless dimensioned otherwise.

Figure 56. Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA with Stamped Lid

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—
SD_IMP_CAL_RX	L28	I	200Ω to GND	—
SD_IMP_CAL_TX	AB26	I	100Ω to GND	—
SD_PLL_TPA	U26	O	—	24

Notes:

1. All multiplexed signals are listed only once and do not re-occur. For example, LCS5/DMA_REQ2 is listed only once in the local bus controller section, and is not mentioned in the DMA section even though the pin also functions as DMA_REQ2.
2. Recommend a weak pull-up resistor (2–10 kΩ) be placed on this pin to OV_{DD}.
3. A valid clock must be provided at POR if TSEC4_TXD[2] is set = 1.
4. This pin is an open drain signal.
5. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pullup or active driver is needed.
6. Treat these pins as no connects (NC) unless using debug address functionality.
7. The value of LA[28:31] during reset sets the CCB clock to SYSCLK PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See Section 20.2, “CCB/SYSCLK PLL Ratio.”
8. The value of LALE, LGPL2, and LBCTL at reset set the e500 core clock to CCB clock PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See the Section 20.3, “e500 Core PLL Ratio.”
9. Functionally, this pin is an output, but structurally it is an I/O because it either samples configuration input during reset or because it has other manufacturing test functions. This pin therefore is described as an I/O for boundary scan.
10. This pin functionally requires a pull-up resistor, but during reset it is a configuration input that controls 32- vs. 64-bit PCI operation. Therefore, it must be actively driven low during reset by reset logic if the device is to be configured to be a 64-bit PCI device. See the *PCI Specification*.
11. This output is actively driven during reset rather than being three-stated during reset.
12. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
13. These pins are connected to the V_{DD}/GND planes internally and may be used by the core power supply to improve tracking and regulation.
14. Internal thermally sensitive resistor.
15. No connections must be made to these pins if they are not used.
16. These pins are not connected for any use.
17. PCI specifications recommend that a weak pull-up resistor (2–10 kΩ) be placed on the higher order pins to OV_{DD} when using 64-bit buffer mode (pins PCI_AD[63:32] and PCI1_C_BE[7:4]).
19. If this pin is connected to a device that pulls down during reset, an external pull-up is required to drive this pin to a safe state during reset.
20. This pin is only an output in FIFO mode when used as Rx flow control.
24. Do not connect.

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ64}}$/$\overline{\text{PCI2\_FRAME}}$	AF14	I/O	OV_{DD}	2, 5, 10
$\overline{\text{PCI1\_ACK64}}$/$\overline{\text{PCI2\_DEVSEL}}$	V15	I/O	OV_{DD}	2
PCI2_CLK	AE28	I	OV_{DD}	39
$\overline{\text{PCI2\_IRDY}}$	AD26	I/O	OV_{DD}	2
$\overline{\text{PCI2\_PERR}}$	AD25	I/O	OV_{DD}	2
$\overline{\text{PCI2\_GNT}}$[4:1]	AE26, AG24, AF25, AE25	O	OV_{DD}	5, 9, 35
$\overline{\text{PCI2\_GNT0}}$	AG25	I/O	OV_{DD}	—
$\overline{\text{PCI2\_SERR}}$	AD24	I/O	OV_{DD}	2,4
$\overline{\text{PCI2\_STOP}}$	AF24	I/O	OV_{DD}	2
$\overline{\text{PCI2\_TRDY}}$	AD27	I/O	OV_{DD}	2
$\overline{\text{PCI2\_REQ}}$[4:1]	AD28, AE27, W17, AF26	I	OV_{DD}	—
$\overline{\text{PCI2\_REQ0}}$	AH25	I/O	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—
$\overline{\text{MWE}}$	E7	O	GV_{DD}	—
$\overline{\text{MCAS}}$	H7	O	GV_{DD}	—
$\overline{\text{MRAS}}$	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
$\overline{\text{MCS}}$[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
$\overline{\text{MCK}}$[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—

Table 87. Part Numbering Nomenclature (continued)

MPC	*nnnnn*	*t*	*pp*	*ff*	*c*	*r*
Product Code	**Part Identifier**	**Temperature**	**Package[1, 2, 3]**	**Processor Frequency[4]**	**Core Frequency**	**Silicon Version**
MPC	8545E	Blank = 0 to 105°C C = –40° to 105°C	HX = CBGA VU = Pb-free CBGA PX = PBGA VT = Pb-free PBGA	AT = 1200 AQ = 1000 AN = 800	G = 400	Blank = Ver. 2.0 (SVR = 0x80390220) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x80390231)
	8545					Blank = Ver. 2.0 (SVR = 0x80310220) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x80310231)
	8543E			AQ = 1000 AN = 800		Blank = Ver. 2.0 (SVR = 0x803A0020) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x803A0031)
	8543					Blank = Ver. 2.0 (SVR = 0x80320020) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x80320031)

Notes:

1. See Section 19, “Package Description,” for more information on available package types.
2. The HiCTE FC-CBGA package is available on only Version 2.0 of the device.
3. The FC-PBGA package is available on only Version 2.1.1, 2.1.2, and 2.1.3 of the device.
4. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.
5. This speed available only for silicon Version 2.1.1, 2.1.2, and 2.1.3.